NSN 5962-01-491-2679

Memory Microcircuit - Page 1 of 1



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Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+155.0 degrees celsius
End Application:
Radar threat emitter an/mst-t1; m3p reu-l
Features Provided:
High speed and low power and asynchronous
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Product Name:
Cmos asynchronous fifo
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
20.00 nanoseconds af output megawatts
Memory Device Type:
First-in first-out
Special Features:
2, 048 x 9-bit; thin ceramic dip
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
28 printed circuit
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:
A458a0